



DGD2103M

HALF-BRIDGE GATE DRIVER IN SO-8

Description

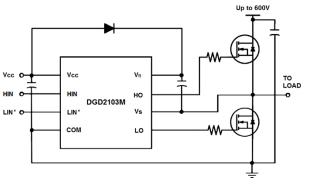
The DGD2103M is a high-voltage/high-speed gate driver capable of driving N-channel MOSFETs and IGBTs in a half-bridge configuration. High-voltage processing techniques enable the DGD2103M's high side to switch to 600V in a bootstrap operation.

The DGD2103M logic inputs are compatible with standard TTL and CMOS levels (down to 3.3V) to interface easily with controlling devices. The driver output features high-pulse current buffers designed for minimum driver cross conduction. DGD2103M has a fixed internal deadtime of 420ns (typical).

The DGD2103M is offered in the SO-8 package and operates over an extended -40°C to +125°C temperature range.

Applications

- **DC-DC Converters**
- **DC-AC** Inverters
- **AC-DC Power Supplies**
- Motor Controls
- **Class D Power Amplifiers**



Typical Configuration

Ordering Information (Note 4)

Part Number	Marking	Reel Size (inch)	Tape Width (mm)	Quantity per Reel
DGD2103MS8-13	DGD2103M	13	12	2,500

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



] | = Manufacturer's Marking DGD2103M = Product Type Marking Code YY = Year (ex: 21 = 2021) WW or WW- = Week (01 to 53)

Features

- Floating High-Side Driver in Bootstrap Operation to 600V
- Drives Two N-Channel MOSFETs or IGBTs in a Half-Bridge Configuration
- Designed for Enhanced Performance in Noisy Motor Applications
- 290mA Source/600mA Sink Output Current Capability
- Outputs Tolerant to Negative Transients
- Internal Dead Time of 420ns to Protect MOSFETs
- Wide Low-Side Gate Driver Supply Voltage: 10V to 20V •
- Logic Input (HIN and LIN*) 3.3V Capability •
- Schmitt Triggered Logic Inputs
- Undervoltage Lockout for V_{CC} (Logic and Low Side Supply)
- Extended Temperature Range: -40°C to +125°C
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts gualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative.

https://www.diodes.com/guality/product-definitions/

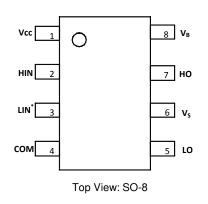
Mechanical Data

- Case: SO-8 (Standard)
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminals: Finish-Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.075 grams (Approximate)





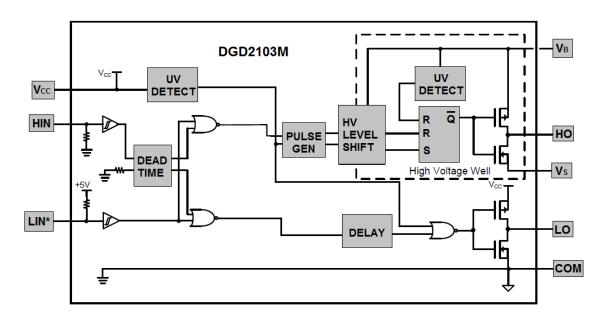
Pin Diagrams



Pin Descriptions

Pin Number	Pin Name	Function	
1	Vcc	Logic and Low-Side Supply	
2	HIN	Logic Input for High-Side Gate Driver Output in Phase with HO	
3	LIN*	Logic Input for Low-Side Gate Driver Output out of Phase with LO	
4	COM	Low-Side and Logic Return	
5	LO	Low-Side Gate Drive Output	
6	Vs	High-Side Floating Supply Return	
7	HO	High-Side Gate Drive Output	
8	VB	High-Side Floating Supply	

Functional Block Diagram





Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
High-Side Floating Supply Voltage	VB	-0.3 to +624	V
High-Side Floating Supply Offset Voltage	Vs	V _B -24 to V _B +0.3	V
High-Side Floating Output Voltage	Vно	Vs-0.3 to V _B +0.3	V
Offset Supply Voltage Transient	dVs / dt	50	V/ns
Low-Side Fixed Supply Voltage	V _{CC}	-0.3 to +24	V
Low-Side Output Voltage	VLO	-0.3 to Vcc+0.3	V
Logic Input Voltage (HIN and LIN*)	V _{IN}	-0.3 to V _{CC} +0.3	V

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation Linear Derating Factor (Note 5)	PD	0.625	W
Thermal Resistance, Junction to Ambient (Note 5)	Reja	200	°C/W
Operating Temperature	TJ	+150	
Lead Temperature (Soldering, 10s)	TL	+300	°C
Storage Temperature Range	T _{STG}	-55 to +150	

Note: 5. When mounted on a standard JEDEC 2-layer FR-4 board.

Recommended Operating Conditions

Parameter	Symbol	Min	Мах	Unit
High Side Floating Supply Absolute Voltage	VB	V _S + 10	V _S + 20	V
High Side Floating Supply Offset Voltage	Vs	(Note 6)	600	V
High Side Floating Output Voltage	Vно	Vs	VB	V
Low Side Supply Voltage	V _{CC}	10	20	V
Low Side Output Voltage	VLO	0	Vcc	V
Logic Input Voltage (HIN & LIN*)	V _{IN}	0	6	V
Ambient Temperature	TA	-40	+125	°C

Note: 6. Logic operation for V_S of -5V to +600V.



DC Electrical Characteristics (V_{BIAS} (V_{CC}, V_{BS}) = 15V, @T_A = +25°C, unless otherwise specified.) (Note 7)

Parameter	Symbol	Min	Тур	Max	Unit	Condition
Logic "1" (HIN) & Logic "0" (LIN*) Input Voltage	VIH	2.5	—		V	V _{CC} = 10V to 20V
Logic "0" (HIN) & Logic "1" (LIN*) Input Voltage	VIL	_	—	0.8	V	V _{CC} = 10V to 20V
High Level Output Voltage, V _{BIAS} - V _O	Vон	-	0.05	0.2	V	$I_0 = 2mA$
Low Level Output Voltage, V _O	V _{OL}		0.02	0.1	V	$I_0 = 2mA$
Offset Supply Leakage Current	Ilk	-	—	50	μΑ	$V_{B} = V_{S} = 600V$
Quiescent V _{BS} Supply Current	I _{BSQ}	-	60	100	μΑ	$V_{IN} = 0V \text{ or } 5V$
Quiescent Vcc Supply Current	lccq		350	500	μA	$V_{IN} = 0V \text{ or } 5V$
Logic "1" Input Bias Current	I _{IN+}	_	3	10	μA	HIN = 5V, LIN* = 0V
Logic "0" Input Bias Current	l _{IN-}		_	5	μΑ	HIN = 0V, LIN* = 5V
Vcc Supply Undervoltage Positive Going Threshold	VCCUV+	8.0	8.9	9.8	V	—
V _{CC} Supply Undervoltage Negative Going Threshold	V _{CCUV-}	7.4	8.2	9.0	V	—
VBS Supply Undervoltage Positive Going Threshold	VBSUV+	4.5	5.5	6.5	V	_
V _{BS} Supply Undervoltage Negative Going Threshold	V _{BSUV-}	4.2	5.2	6.2	V	-
Output High Short Circuit Pulsed Current	Io+	130	290	_	mA	$V_O = 0V, P_W \le 10 \mu s$
Output Low Short Circuit Pulsed Current	I _{O-}	270	600	—	mA	$V_{0} = 15V, P_{W} \leqslant 10 \mu s$

Notes: 7. The V_{IN} and I_{IN} parameters are applicable to the two logic pins: HIN and LIN*. The V_O and I_O parameters are applicable to the respective output pins: HO and LO.

AC Electrical Characteristics (V_{BIAS} (V_{CC}, V_{BS}) = 15V, C_L = 1000pF, @T_A = +25°C, unless otherwise specified.)

Parameter	Symbol	Min	Тур	Max	Unit	Condition
Turn-On Propagation Delay	ton	—	680	820	ns	$V_S = 0V$
Turn-Off Propagation Delay	toff	—	150	220	ns	V _S = 600V
Delay Matching, HO & LO Turn-On / Turn-Off	tdм	—	_	60	ns	—
Turn-On Rise Time	tR	—	70	170	ns	$V_S = 0V$
Turn-Off Fall Time	tF	_	35	90	ns	$V_S = 0V$
Deadtime: tot lo-ho & tot ho-lo	tdт	300	420	650	ns	—



Timing Waveforms

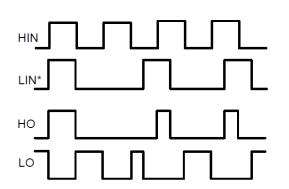
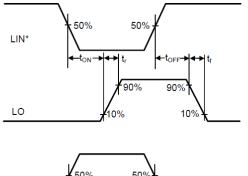


Figure 1. Input / Output Timing Diagram



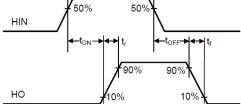


Figure 2. Switching Time Waveform Definitions

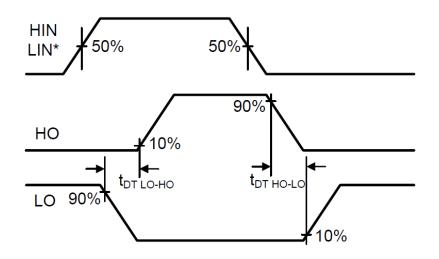


Figure 3. Deadtime Waveform Definitions



Typical Performance Characteristics (Vcc = 15V, @TA = +25°C, unless otherwise specified.)

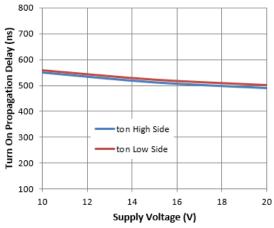


Figure 4. Turn-on Propagation Delay vs. Supply Voltage

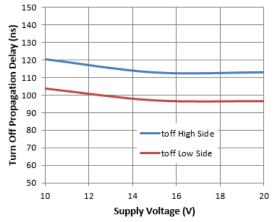
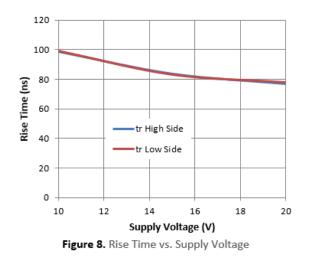


Figure 6. Turn-off Propagation Delay vs. Supply Voltage



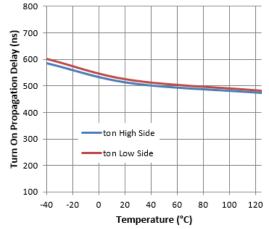


Figure 5. Turn-on Propagation Delay vs. Temperature

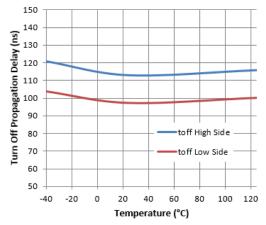
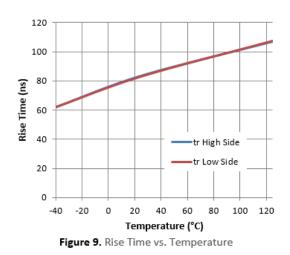


Figure 7. Turn-off Propagation Delay vs. Temperature





Typical Performance Characteristics (continued)

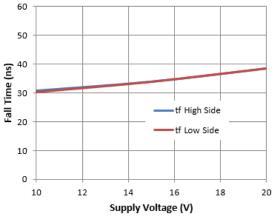


Figure 10. Fall Time vs. Supply Voltage

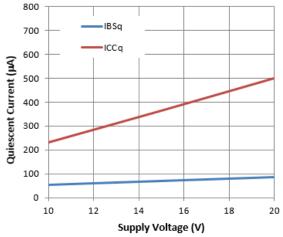


Figure 12. Quiescent Current vs. Supply Voltage

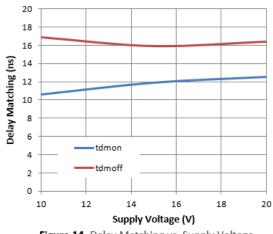


Figure 14. Delay Matching vs. Supply Voltage

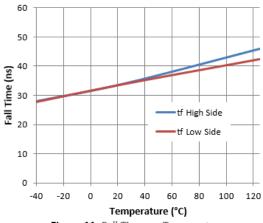
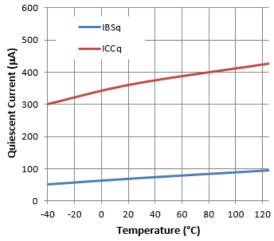


Figure 11. Fall Time vs. Temperature





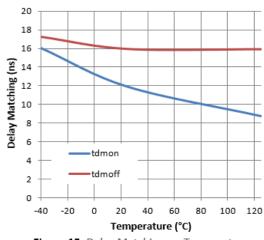


Figure 15. Delay Matching vs. Temperature



Typical Performance Characteristics (continued)

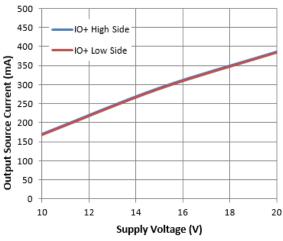


Figure 16. Output Source Current vs. Supply Voltage

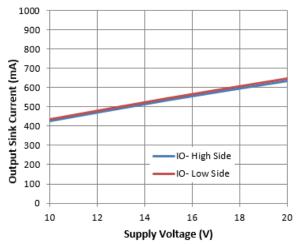


Figure 18. Output Sink Current vs. Supply Voltage

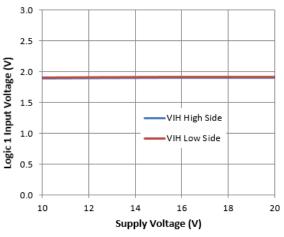


Figure 20. Logic 1 Input Voltage vs. Supply Voltage

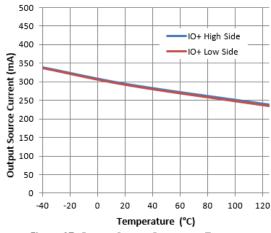
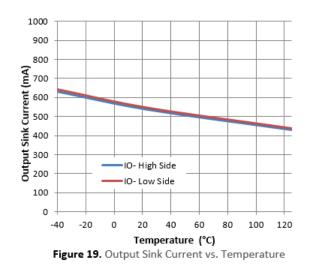
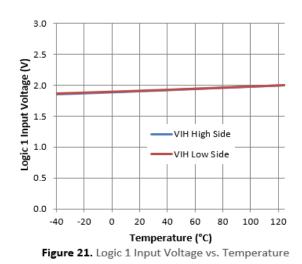


Figure 17. Output Source Current vs. Temperature







Typical Performance Characteristics (continued)

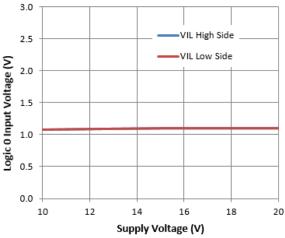


Figure 22. Logic 0 Input Voltage vs. Supply Voltage

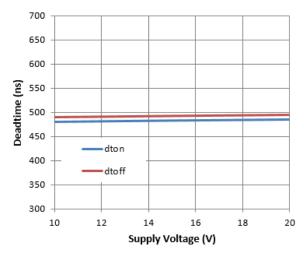
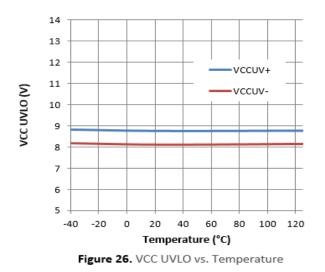


Figure 24. Deadtime vs. Supply Voltage



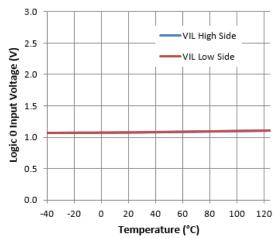


Figure 23. Logic 0 Input Voltage vs. Temperature

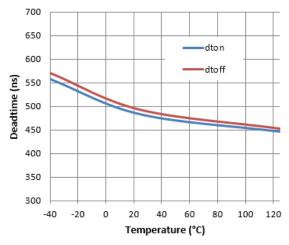


Figure 25. Deadtime vs. Temperature

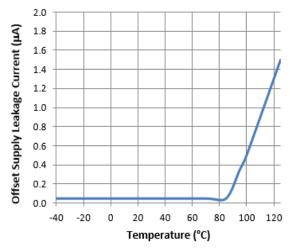
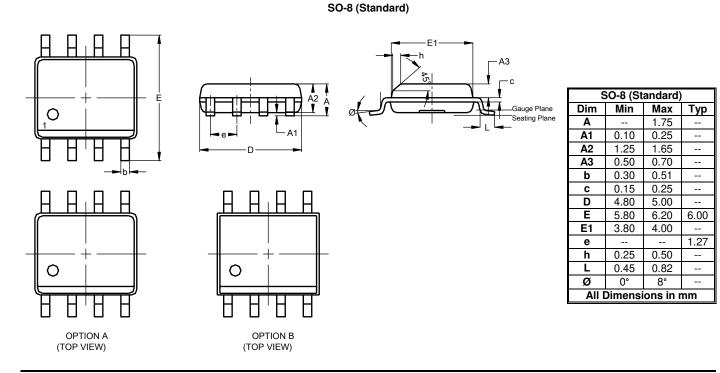


Figure 27. Offset Supply Leakage Current vs. Temperature



Package Outline Dimensions

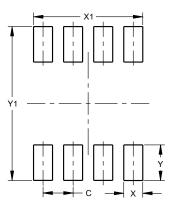
Please see http://www.diodes.com/package-outlines.html for the latest version.



Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SO-8 (Standard)



Dimensions	Value (in mm)
С	1.27
Х	0.802
X1	4.612
Y	1.505
Y1	6.50

Note : For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device Terminals and PCB tracking.



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